

400V High Voltage NPN Transistor

FEATURES

- Epitaxial Planar Type
- NPN Silicon Transistor
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

APPLICATION

- Consumer electronics
- High voltage switching
- High voltage driver









Notes: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Collector-Base Voltage	V _{CBO}	400	V	
Collector-Emitter Voltage	V _{CEO}	400	V	
Emitter-Base Voltage	V _{EBO}	6	V	
Collector Current (DC)	Ι _C	300	mA	
Power Total Dissipation @ T _A =25 ^o C	P _D	0.225	W	
Maximum Operating Junction Temperature	TJ	+150	°C	
Storage Temperature Range	T _{STG}	-55 to +150	°C	

Note: Single pulse, $Pw \le 380\mu s$, $Duty \le 2\%$

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	ТҮР	UNIT		
Junction to Ambient Thermal Resistance	R _{eja}	556	°C/W		
Junction to Case Thermal Resistance	R _{eJC}	185	°C/W		



ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)							
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT	
Static (Note 1)							
Collector-Base Breakdown Voltage	$I_{C} = 50 \text{uA}, I_{E} = 0$	BV _{CBO}	400			V	
Collector-Emitter Breakdown Voltage	$I_{C} = 1 \text{ mA}, I_{B} = 0$	BV _{CEO}	400			V	
Emitter-Base Breakdown Voltage	$I_{E} = 50 uA, I_{C} = 0$	BV_{EBO}	6			V	
Collector Cutoff Current	$V_{CB} = 400 V, I_{E} = 0$	I _{CBO}			10	μA	
Collector-Emitter Reverse Current	V_{CE} = 300V, R_{EB} =4k Ω	I _{CER}			20	nA	
Emitter Cutoff Current	$V_{EB}=6V, I_{C}=0$	I _{EBO}			10	μA	
Collector-Emitter Saturation Voltage	$I_{C} = 10 \text{mA}, I_{B} = 1 \text{mA}$	V _{CE(SAT)}		0.1	0.5	V	
Base-Emitter Saturation Voltage	$I_{C} = 10 \text{mA}, I_{B} = 1 \text{mA}$	$V_{BE(SAT)}$			1.5	V	
DC Current Transfer Ratio	$V_{CE} = 10V, I_{C} = 10mA$	h _{FE}	100		270		
Dynamic ^(Note 2)							
Transition Frequency	V _{CE} =10V, I _C =-10mA, f=10MHz	f⊤		20		MHz	
Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 1MHz$	C _{ob}		7		pF	

Note:

1. Pulse test: ≤380µs, duty cycle ≤2%

2. For DESIGN AID ONLY, not subject to production testing

ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSC4505CX RFG	SOT-23	3,000pcs / 7" Reel

TSC4505CX Taiwan Semiconductor



ELECTRICAL CHARACTERICS CURVES (T_A=25°C, unless otherwise noted)







Figure 5. Safe Operating Area





Figure 4. Power Derating Curve







PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



101	nth Code	Э					
1	=Jan	2	=Feb	3	=Mar	4	=Apr
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8 = Aug 5 =May 6 =Jun 7 =Jul **9** =Sep A =Oct **C** =Dec **B** =Nov



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